



Arabinda Nayak

Curriculum Vitae (March 14, 2020)

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APPOINTMENTS

Dean of Faculty of Natural and Mathematical Sciences Presidency University, Kolkata	2016-2019
Professor of Physics Presidency University, Kolkata	2012-till date
Associate Professor of Physics Presidency College, Kolkata (2009-2010) Presidency University, Kolkata (2010-2012)	2009-2012
Reader in Physics Presidency College, Kolkata	2006-2009
Lecturer (Sr. Scale) in Physics Presidency College, Kolkata	2002-2006
Lecturer in Physics Darjeeling Govt. College, Darjeeling	1997-2002
Lecturer in Physics North Regional Institute of Science & Technology, Nirjuli, AP	1996-1997
Postdoctoral Fellow (RA, CSIR) Material Science Center, IIT Kharagpur	1993-1996

[Research on the preparation and characterization of Diamond and Diamond-Like-Carbon \(DLC\) Films](#)

EDUCATION

PhD Materials Science 1988-1993

Materials Science Center, IIT, Kharagpur

“Studies on Structural, Electrical and Optical Properties of Electron Beam Deposited Zn₃P₂-Cd₃P₂ Thin Films”

Thesis advisors: Professor D. R. Rao and Professor H. D. Banerjee

MSc Physics (5-year Integrated) 1982-1987

Department of Physics, IIT, Kharagpur

NATIONAL ELIGIBILITY TEST STATUS

- Joint CSIR - UGC NET (1988)
- GATE (1988)

SOCIETY MEMBERSHIP

- Life member, Indian Association for the Cultivation of Science, Kolkata
- Life Member, Materials Research Society of India (MRSI)

FIELD OF SPECILZATION

- Experimental Condensed Matter Physics & Materials Science
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MAJOR RESEARCH INTEREST

- Synthesis and Evaluation of Thin Films
 - Development of Ge and ZnO-based nanomaterials
 - Diamond & Diamond-Like-Carbon Films
 - Polymer-Inorganic Hybrid nanocomposites
 - Development of Zinc-Tin-Phosphide based chalcopyrites thin films for solar cell application
 - Photodetectors & Multi-junction Solar Cells
 - Computational Materials Science & Optical Response of Functional Materials
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MY RESEARCH LABORATORY

- I have set up one Solid State and Materials Science research laboratory for the deposition and evaluation of ultra fine (down to 5 nm) germanium (Ge) particles, ZnO nanocrystals, thin film and crystalline compound

semiconductors and conducting polymer-inorganic hybrid nanocomposites for device applications. The equipped with an Ionized Cluster Beam (ICB) deposition system for the growth of Ge nanoparticles (funded by DST, Govt. of India). Recently, one Bridgman growth apparatus has been installed for the growth of ZnSnP₂ single crystal (funded by UGC).

- An experimental set up for the measurement of ac conductivity and dielectric response for the nanocomposite materials at elevated temperatures has also been designed by me and fabricated under the FRPDF grant provided by the Presidency University.
- The laboratory also equipped with supporting instruments for material preparation such as Centrifuge (up to 5000 rpm), Spin Coating system, UV light source (200 W), magnetic stirrer with hot plate etc. (purchased from FRPDF grant).

SUPERVISING OF RESEARCH SCHOLARS FOR Ph.D DEGREE

1. **Tamaghna Maitra (NET, UGC).** Research Proposal: Metalorganic Vapor Phase Epitaxial (MOVPE) growth of Ge/In_xGa_{1-x}P multi quantum wells
2. **Sukhendu Mukherjee (NET, UGC Project).** Research Proposal: Development, Synthesis and Characterization of ZnSnP₂ Chalcopyrite Thin Film for Photovoltaic Devices
3. **Banasree Sadhukhan (Part time).** Research Proposal: Optical conductivity and dielectric function of NiPt alloy systems. (Awarded, 2019).

SUPERVISION OF JRF/SRF

- **Ipsita Halder (SRF, CSIR, 2015-2015).** Research: Dielectric, ac conductivity relaxation and magnetoresistive behaviors of BaTiO₃-ppy nanocomposites

Research Finding: Nano crystalline BaTiO₃ and polypyrrole (ppy)-BaTiO₃ hybrid nanocomposites have been synthesized using chemical oxidative polymerization method. Microstructure and crystallinity of the hybrids are studied using field emission scanning electron microscope (FE-SEM), high resolution transmission electron microscope (HRTEM) and X-ray

diffraction (XRD) technique. As prepared BaTiO₃ are rod-like, while PPY-BaTiO₃ nanocomposites indicate the formation of bulging agglomerates of spherical particles with various sizes (40-50 nm). Dielectric constants at room temperature of the composites have largely enhanced (up to 6000). The hybrid composite shows grain boundary relaxation in the frequency range (42 Hz-5 MHz). Three dimensional (3D) variable range hopping (VRH) with high localization of charge carriers (Mott temperature ≈ 8725658 K) is observed in the temperature dependent conductivity evaluation of composite system. Negative magnetoresistance (MR $\approx 4.3\%$) has been measured at 1 T. The observed MR is explained with the help of forward interference model.

MAJOR RESEARCH PROJECT (COMPLETED)

- **Development of Tetragonal Ge-nanocrystals by Ionized Cluster Beam Deposition Technique: A New Light Emitting Materials for Future Optoelectronic.**

Sponsoring Authority: DST, Govt. of India. D. D. No. SR/ S2/ CMP - 53/ 2003. Amount: 24 Lakh. Duration: 11/10/2006 to 10/10/2009.

Research Finding: We have successfully deposited Ge-NCs on Si (100) and quartz substrates by ICB deposition technique developed in our laboratory. Ge nanocrystals mostly with tetragonal phase were obtained when grown using neutral cluster. A composite phase containing both tetragonal and high percentage of diamond cubic structure of Ge-NCs could be grown when the clusters were ionized and subsequently accelerated with potential greater than 1.50 kV. HRTEM techniques were used to study the microstructure of the crystallites. Optical band gap of the Ge-films were in the range 1.55 eV-1.60 eV. The UV light illumination has a pronounced effect on the optical spectra of the non-cubic Ge-NCs.

Germanium nanocrystals embedded between amorphous Al₂O₃ layers deposited by ICB deposition technique exhibited distinct microcrystalline structures with progressively lowering of disorder with thermal treatment. Such NCs are promising for the non-volatile memory devices.

- **Polymer-Inorganic Hybrid Nanocomposites - Preparation, Characterization and their Potential as Nanodielectrics.**

Sponsoring Authority: CSIR, New Delhi. Sanction No: CSIR-01(2342)/09/EMR-II.

Amount: 13.68 Lakh. Duration: from 01.11.2009 to 31.10.2013. (In collaboration with Department of Chemistry).

Research Finding: A nanocomposite of PNVC and nano-dimensional Fe_3O_4 (PNVC- Fe_3O_4) was prepared by insitu solid state polymerization of N-vinylcarbazole by Fe_3O_4 at 65°C . PPY encapsulated PNVC- Fe_3O_4 nanocomposite was synthesized via polymerization of PY in an aqueous suspension of PNVC- Fe_3O_4 composite in presence of KPS. The formations of PNVC and of PPY in the PPY-(PNVC- Fe_3O_4) system were confirmed by FTIR analysis. TGA and DTA analyses showed the thermal stability trend as $\text{Fe}_3\text{O}_4 > \text{PNVC-Fe}_3\text{O}_4 > \text{PPY-(PNVC-Fe}_3\text{O}_4) > \text{PNVC}$. HRTEM studies revealed that the PPY-(PNVC- Fe_3O_4) nanoparticles have an average grain size of 37 nm with the Fe_3O_4 nanoparticles fairly well-dispersed in the composite matrix. The SEM study showed a spherical morphology of PPY-(PNVC- Fe_3O_4) particles. XRD studies also confirmed the particle size to be 37 nm. The dielectric constants of PNVC- Fe_3O_4 and the PPY- Fe_3O_4 systems (110-400) were improved relative to the base polymers. In contrast, the PPY encapsulated PNVC- Fe_3O_4 nanocomposites showed significantly higher values of dielectric constant (>1000). The interfaces between polymer and oxide layers play crucial roles for enhancing dielectric properties of the system. The ac conductivity was found to be independent of frequency in the range 10^2 to 10^3 Hz for all the nanocomposites and rise thereafter appreciably in the frequency range of 1 kHz to 25 kHz.

- **Development, Synthesis and Characterization of ZnSnP_2 Chalcopyrite Thin Film for Photovoltaic Devices.**

Sponsoring Authority: UGC, New Delhi. Sanction No.MRP-MAJOR-MATE-2013-16190.

Amount: 11.91 Lakh. Duration: from 01.07.2015 to 31.06.2018.

ZnSnP₂, a member of II-IV-V₂ group compound semiconductors, has recently attracted much attention as a potential absorbing material for thin film solar cell applications. Recent theoretical calculations on the electronic structure of ZnSnP₂ indicate that it possesses an ordered chalcopyrite structure which can transform to a disordered sphalerite structure at high temperature (720°C) with a variation of room temperature optical band gaps from 1.70 eV to 0.75 eV. In the chalcopyrite structure (bandgap = 1.70 eV), Zn and Sn occupy on specific sites of the fcc lattice, while in the sphalerite structure (bandgap = 0.75 eV) they are randomly distributed on fcc sites giving rise to disorder phase. This feature indicates that bandgap of ZnSnP₂ could be tuned from 0.75 eV to 1.70 eV by controlling growth temperature and hence the atomic configuration. The grading of band gaps from low to high values could be achieved by growing an initial layer at a higher temperature corresponding to lower band gap and then the subsequent layers are grown at relatively lower temperatures. The exact growth temperatures and their relation to the band gap values of ZnSnP₂ need to be optimized properly. Thus, the band gap tuning facilitates the fabrication of various homo p-n junctions by properly choosing a definite phase of ZnSnP₂ and doping. Interestingly, an optical band gap of 1.68 eV, which is close to the optimum band gap (~ 1.50 eV) at the Shockley-Quisser limit, has been reported. Moreover, other advantages such as ternary ZnSnP₂ is low-toxic, the constituent elements for the preparation of ZnSnP₂ are earth abundant and inexpensive and high absorption coefficient (> 10⁴ cm⁻¹) above 1.60 eV, find ZnSnP₂ a potential alternative for photovoltaic device applications. It has excellent lattice matching with GaAs substrates. The growth of ZnSnP₂ thin films have been reported previously by co-evaporation and in ultrahigh vacuum by molecular beam epitaxy (MBE). Recently, ZnSnP₂ based thin-film solar cell with ZnSnP₂ absorber is fabricated by phosphidation method under the variation of Zn/Sn atomic ratio. The solar cell parameters (J_{sc} = 2.63 mA/cm², V_{oc} = 3.7 mV, FF = 27.2%, and conversion efficiency = 0.0027%) have been measured using near-stoichiometric ZnSnP₂ as the absorber layer. In the study, the authors found two different current areas. Low-current area is attributed to the

presence of Zn_3P_2 secondary phase forming the shunt paths while the high-current area (0.014 cm^2) with efficiency = 0.021%, $J_{sc} = 5.03 \text{ mA/cm}^2$ is obtained due to the formation of pure $ZnSnP_2$ phase. The energy band gap of $ZnSnP_2$ thin film prepared by phosphidation method was reported as 1.38 eV indicating the growth of sphalerite $ZnSnP_2$ structure with appropriate variation of Zn/Sn atomic ratio. In few cases, J-V characteristics of the hetero-junction solar cell [Al/AZO/ $ZnO/CdS/ZnSnP_2/Mo$] have been studied. The performance of the fabricated cell was found quite low (conversion efficiency is 0.087%). Necessary modifications of the cell structure to achieve better performances such as improvement of the resistance of the hetero-interfaces and the use of appropriate buffer materials have been suggested.

Though some limited studies have been made by several researchers on the preparation of crystalline bulk material and thin epitaxial layer, detailed understanding of optical and electrical properties, the nature of native defects responsible for top-type conductivity in $ZnSnP_2$ are still obscure. In $ZnSnP_2$ thin film, zinc vacancies or zinc-on-tin sites are considered as acceptor which is responsible for p-type conductivity. Defects introduce localized levels in the energy gap of $ZnSnP_2$ and other compound semiconductors through which they control solar cell device performance, efficiency and reliability. Native defects such as vacancies, self-interstitials, and antisite defects often act as unintended dopants or compensate intentionally introduced dopants of these materials. In addition, native defects as well as contaminant impurities also limit the efficiency of light-emission in $ZnSnP_2$ and related materials. Thus, it is of great significance to study the nature and behaviour of such defects under different conditions.

MAJOR RESEARCH PROJECT (ON GOING)

- **Growth and realization of ferroelectric-photovoltaic effect in $ZnSnS_3$ thin films for solar cell and photodetector applications.**
Sponsoring Agency: SERB-DST, Govt. of India; Amount sanctioned: Rs. 24.46 lakh. Duration: 26 December 2019-25 December 2022.

Ferroelectric materials with their switchable polarization by electrical field have been considered as next generation photovoltaic applications. This research proposal is mainly directed towards the synthesis, fabrication and characterization of a theoretically predicted new photovoltaic material based on ferroelectric LN- ZnSnS₃, thin films of which will be grown on an epitaxial GaN coated silicon substrate using spray pyrolysis technique. It is shown in theoretical study that the photovoltaic property of LN-ZnSnS₃ would be enhanced owing to its optimum band gap (~1.3 eV), lower hole effective mass (0.35m₀), large intrinsic polarization (~59 μC/cm²) and high dielectric constant (10.30) compared to conventional ferroelectric materials which is beneficial for applications in solar cell and broadband photodetector devices. In this proposed project, the microstructural, optical and electrical properties of ZnSnS₃ films are to be examined confirming their composition and phases, band gap in the visible-near infrared wavelength and the ferroelectric characteristics at room temperature. The ferroelectric-photovoltaic effect for this material will be evaluated for the first time. The photosensitivity, transient response of photocurrent under constant bias with periodically exposure of visible-near infrared light (300nm-1100nm) and the current-voltage curves under illumination would be demonstrated for the fabricated LN- ZnSnS₃ thin films. Nickel metal has been chosen for ohmic contact for this material. The short-circuit photocurrent and open-circuit photovoltage are to be switched by applying a poling voltage and their dependency on the power of illuminating light would be studied in details.

OTHER COLLABORATIVE RESEARCH PROJECTS (ON GOING)

- 1. Metalorganic Vapor Phase Epitaxial (MOVPE) growth of Al_{0.3}Ga_{0.7}As/GaAs multi quantum wells (MQW) (in collaboration with Dr. S. Bhunia, Surface Physics & Materials Science Division, SINP, Kolkata)**

Proposal: Nowadays the use of “quantum devices” based on compound semiconductors has caused a great impact on our daily life. Very high end conceptual devices based on quantum wells such as quantum cascade lasers (QCL), vertical cavity surface emitting lasers (VCSEL), quantum well infrared photodetectors (QWIP), resonant tunneling diodes (RTD) etc have been demonstrated. The quantum wells employed in such devices need to be of high quality, and precisely controlled thickness. High quality refers to smooth interfaces, few non-intentional incorporated impurities and high

photoluminescence efficiency. Such high quality QWs are also important in realizing two-dimensional electron gases and studying physical phenomena associated with them. In this project work, we will study MOVPE growth of GaAs/Al_{1-x}Ga_xAs QWs and study the effect of interface roughness on their optical emission properties.

2. **Temperature dependent dielectric properties and ac conductivity relaxation in NiO.V₂O₅ - PEDOT nanocomposites (in collaboration with Dr. U.C. Ghosh, Former Associate Professor, Department of Chemistry, Presidency University).**

Proposal: Triclinic nickel vanadium mixed oxide (NiO.V₂O₅) with particle size 80-120 nm will be synthesized via combined sol-gel-incineration method. This mixed oxide will be reinforced into the polyethylene dioxythiophene (PEDOT) matrix and characterized using x-ray diffraction (XRD), high resolution transmission electron microscopy (HRTEM), Fourier transform infrared spectroscopy (FTIR) and temperature dependent dielectric constant and ac conductivity measurements. The roll of thermally activated polarons with different activation energies on the electrical conduction in the PEDOT – NiO.V₂O₅ nanocomposite will be investigated.

3. **Preparation, characterization and dielectric, ac conductivity with electrochemical behavior of strontium zirconate (in collaboration with Dr. U. C. Ghosh, Former Associate Professor, Department of Chemistry, Presidency University).**
4. **Microstructural, electrical relaxation and magnetic characteristics of GdFeO₃-SmFeO₃ mixed improper multiferroic materials (for MSc project).**
5. **(A) Effect of disorder on the optical response of NiPt and Ni₃Pt alloys & (B) Band-gap tuning and optical response of two-dimensional Si_xC_{1-x}: A first-principles real-space study of disordered two-dimensional materials (in collaboration with Prof. Abhijit Mookerjee, Professor Emeritus, S.N. Bose National Center for Basic Sciences, Kolkata).**

Proposal: In this theoretical and computational studies, we proposed a detailed study of the effect of chemical disorder on the optical response of $\text{Ni}_{1-x}\text{Pt}_x$ ($0.1 < x < 0.75$) and $\text{Ni}_{3(1-x)/3}\text{Pt}_x$ ($0.1 < x < 0.3$). We shall propose a formalism which will combine a Kubo-Greenwood approach with a DFT based tight-binding linear muffin-tin orbitals (TB-LMTO) basis and augmented space recursion (ASR) technique to explicitly incorporate the effect of disorder. We will examine that the chemical disorder has a large impact on optical response of Ni-Pt systems. This same approach will be used to quantitatively analyze the effect of chemical disorder on $\text{Si}_x\text{C}_{1-x}$ beyond the usual Dirac-cone approximation.

6. **Development of KBiFe_2O_5 film for visible light absorbing multiferroic and photovoltaic material: Influence of confining narrow band gap nanoparticles (for Major Research & MSc project).**

Proposal: This research proposal is mainly directed towards the fabrication and characterization of photovoltaic material and device based on the thin polycrystalline films of multiferroic KBiFe_2O_5 (KBFO) whose photovoltaic properties are less studied and understood. Unlike a conventional p-n junction solar cell, the photovoltaic effects in the multiferroic material (like KBFO) is relied on the internal electric field mainly responsible for the separation of photo-generated electron-hole pairs and thereby allows photovoltage higher than the optical band gap of such materials. KBFO films will be deposited on Indium Tin Oxide coated glass and crystalline silicon substrates using spin coating technique with subsequent heat treatment for proper nucleation. Microstructural information will be obtained from X-ray diffraction and transmission electron microscopic studies. On the other hand, optical spectroscopic measurements will be undertaken to determine the absorption coefficient and band gap of the as-grown KBFO films.

In this proposed project, we are mainly interested to study the enhancement of photocurrent and spectral response of the Al- KBiFe_2O_5 -Al structure by embedding narrow band gap (1.2 – 1.3eV) oxide based nano-sized semiconductors (CuO, Ag_2O) in the middle of the KBiFe_2O_5 layer. The fabricated structure not only absorbs more light from visible spectrum for electron-hole pair production but also help to separate them by forming local

p-n heterojunction and lowering the possibility of screening the electric charge carriers. This noble structure with embedding small gap materials is expected to generate more photocurrent with compare to the bare KBiFe_2O_5 (KBFO) single layer. The KBiFe_2O_5 (KBFO) film and source material $\text{CuO}/\text{Ag}_2\text{O}$ for embedding layer will be prepared from the nitrate/hydroxide of their constituent elements by chemical routes. Thermal or electron beam evaporation technique to be utilized for growth of embedding layer ($\text{CuO}/\text{Ag}_2\text{O}$) and necessary electrodes (rectangular or disk shaped) for electrical measurements.

UNDERGRADUATE & POST GRADUATE PROJECTS SUPERVISED

1. Growth, Structural and Electrical Characterization of Zinc Tin Phosphide Thin Films for Solar Cell Applications ([Kiyafa Sultana, MSc, 2013](#)).
2. Growth and Optical Characterization of Zinc Tin Phosphide Thin Films for Solar Cell Applications ([Santanu Adikary, MSc, 2013](#)).
3. Synthesis and microstructural Behaviour of Doped Bismuth Titanate ($\text{Bi}_4\text{Ti}_3\text{O}_{12}$) as Nano Multiferroic Materials ([Arinda Ghosh, MSc, 2014](#)).
4. Magnetic and Electrical Characterization of Doped Bismuth Titanate ($\text{Bi}_4\text{Ti}_3\text{O}_{12}$) Nano Multiferroic Materials ([Sourav Kumar Maji, MSc, 2014](#)).
5. ZnO-Nanorods based Dye Sensitized Solar Cells: Preparation and Implementation ([Sucharita Saha, MSc, 2015](#)).
6. Metal Organic Vapour Phase Epitaxial Growth of $(\text{Al}_y\text{Ga}_{1-y})_z\text{In}_{1-z}\text{P}/(\text{Al}_x\text{Ga}_{1-x})_z\text{In}_{1-z}\text{P}$ Quantum Wells and Study the Effect of Interface Roughness and Alloy Disorder on its Light Emission Properties ([Chandralina Patra, MSc, 2015](#)).
7. X-ray reflectivity analysis of semiconductor multilayer: structural and morphological characterization ([Kaustav Dutta, MSc, 2016](#)).
8. Solving Poisson Equation using FFT: Numerical Solutions of Electrostatic Potentials ([Swadhiti Majhi, BSc, 2016](#)).
9. Study of Equilibrium State of Matter using Molecular Dynamics and Calculation of Thermal Conductivity ([Kanaya Malakar, BSc, 2016](#)).

10. Study of Brownian Motion under Asymmetric Periodic Potential Well (Unmesh Ghorai, BSc, 2017).
11. Electric and Magnetic Properties of Cr Doped GdFeO_3 Multiferroic Perovskite (Mainur Rahaman, MSc, 2017).
12. Realization of Topological Darkness in Nanostructured Plasmonic Materials (Sonali Saha, BSc, 2018)
13. Photovoltaic Effect in Multiferroic KBiFe_2O_5 (Pradip Singha Roy, MSc, 2018).
14. Visible Photodetectors Based on KBiFe_2O_5 Thin Films (Kabirul Hassan, MSc, 2019).

NOW TEACHING (UNDER GRADUATE & POST GRADUATE)

- **PHYS0191**: Mathematical Methods-1 (UG, Odd Semester)
- **PHYS0401**: Mathematical Methods-2 (UG, Even Semester)
- **PHYS0301**: Electromagnetism 1 (UG, Odd Semester)
- **PHYS0491**: Physics Laboratory-3 (UG, Even Semester)
- **PHYS0803**: Solid State Physics 2 (PG, Even Semester)
- **PHYS0902**: Condensed Matter Physics-2 (PG, Odd Semester)
- **PHYS0904**: Physics of Nanostructured Materials (PG, Odd Semester)
- **PHYS0992**: MSc Advanced Laboratory (PG, Odd Semester)

I try to teach all the courses methodically and coherently so as to make the contents enjoyable and acceptable to all students.

1. **Nayak, A.**, Rao, D.R., and Banerjee, H.D. Optical Studies on Electron Beam Deposited Zn₃P₂ Thin Films. *J. Mater. Sci. Lett.* **Vol. 10**, P.403-405 (1991). DOI: 10.1007/BF00728046
2. **Nayak, A.**, Rao, D.R., and Banerjee, H.D. Electrical and Optical Properties of e-Beam Evaporated Zn₃P₂ Thin Films. *Bull. Electrochem.* **Vol.7**, P. 133 – 135 (1991).
3. **Nayak, A.**, Rao, D.R., and Banerjee, H.D. Derivative Spectra of Polycrystalline Zn₃P₂ Thin Films. *Solid State Comm.* **Vol. 78**, P. 149-151 (1991). DOI: 10.1016/0038-1098(91)90272-W
4. Rao, D.R., **Nayak, A.** Preparation and Characterization of Zn₃P₂-Cd₃P₂ Solid Solutions. *J. Mater. Sci.* **Vol. 27**, P. 4389- 4392 (1992). DOI: 10.1007/BF00541571
5. **Nayak, A.** and Rao, D.R. Optical Constant of Zn₃P₂-Cd₃P₂ Thin Films. *Optical Materials.* **Vol. 1**, P. 85-89 (1992). DOI: 0.1016/0925-3467(92)90005-8
6. Rao, D.R., **Nayak, A.** Preparation and Characterization of Cd₃P₂ Thin Films. *J. Appl. Phys.* **Vol. 74**, P. 214 – 218 (1993). DOI: 10.1063/1.354148.
7. **Nayak, A.** and Rao, D.R. Photoluminescence Spectra of Zn₃P₂-Cd₃P₂ Alloy Films. *Appl. Phys. Lett.* **Vol. 63**, P. 592-593 (1993). DOI: 10.1063/1.110779.
8. **Nayak, A.** and Rao, D.R. Electrical Properties of Electron Beam Evaporated Zn₃P₂-Cd₃P₂ Alloy Films. *Matter. Chem. & Phys.* **Vol. 37**, P. 225-229 (1994).
9. **Nayak, A.** and Banerjee, H.D. Bonding Characteristics and Optical Properties of Amorphous Carbon/Diamond Films Deposited by Electron Beam Activated Plasma CVD Method. *Phys. Stat. Sol (a).* **Vol. 149**, P. 629-635 (1995). DOI: 10.1002/pssa.2211490213
10. **Nayak, A.** and Banerjee, H.D. Electron Beam Activated Plasma Chemical Vapour Deposition of Polycrystalline Diamond Films. *Phys. Stat. Sol (a).* **Vol. 151**, P. 107-111 (1995). DOI: 10.1002/pssa.2211510112
11. **Nayak, A.** and Banerjee, H.D. Bonding and Optical Properties of Diamond Like Hydrocarbon Films Deposited by Plasma Decomposition of Acetylene: The Role of Water Vapour Addition. *Mater. Chem. & Phys.* **Vol. 47**, P. 159 – 163 (1997). DOI: 10.1016/S0254-0584(97)80045-4
12. **Nayak, A.** and Banerjee, H.D. Photoluminescence Spectroscopic Investigation on the Quality of Diamond Films Grown in Oxy-Acetylene Combustion Flame. *Thin Solid Films.* **Vol. 298**, P. 14-21 (1997). DOI: 10.1016/S0040-6090(96)09139-0.
13. **Nayak, A.** and Banerjee, H.D. X-Ray Photoelectron Spectroscopy of Zinc Phosphide Thin Films. *Appl. Surf. Sci.* **Vol. 148**, P. 205-210 (1999). DOI: 10.1016/S0169-4332(99)00144-0

14. **Nayak, A.** and Banerjee, H.D. X-Ray Photoelectron Spectra of Zn₃P₂-Cd₃P₂ Alloy Semiconducting Thin Films. *Matter. Chem & Phys.* **Vol. 60**, P. 95-98 (1999).
15. Halder, S.R., **Nayak, A.**, Chini, Roy, S.K., Yamamoto, N. And Bhunia, S. Vapor condensation growth and evaluation mechanism of ZnO nanorod flower structures. *Phys. Stat. Sol. (a).* **Vol. 207**, P.364-369 (2009). DOI: 10.1002/pssa.200925223.
16. Halder, S.R., **Nayak, A.**, Chini, T.K. and Bhunia, S. Strong temperature and substrate effect on ZnO nanorod flower structures in modified chemical vapor condensation growth. *Current Appl. Phys.* **Vol. 10**, P.942-946 (2010). DOI:10.1016/j.cap.2009.11.077.
17. Haldar, I., Kundu, A., Biswas, M., and **Nayak, A.** Preparation and evaluation of a poly (N-vinylcarbazole)-Fe₃O₄ (PNVC-Fe₃O₄) nanocomposite. *Matter.Chem & Phys.* **Vol. 128**, P. 256-264 (2011). DOI: 10.1016/j.matchemphys.2011.03.008.
18. Haldar, I., Biswas, M., and **Nayak, A.** Microstructure, dielectric response and electrical properties of polypyrrole modified poly (N-vinylcarbazole) – Fe₃O₄ (PNVC - Fe₃O₄) nanocomposites. *Synthetic Metals.* **Vol. 161**, P. 1400-1407 (2011). DOI: 10.1016/j-synthmet.2011.05.008.
19. Haldar, I., Biswas, M., and **Nayak, A.** Preparation and evaluation of microstructure, dielectric and conductivity (ac/dc) characteristics of a polyaniline/ poly N-vinylcarbazole/ Fe₃O₄ nanocomposites. *J. Polym. Res.* **Vol. 19**, P. 9951:1-9 (2012). DOI: 10.1007/s10965-012-9951-0.
20. Haldar, I., Biswas, M., **Nayak, A.** and Sinha Ray, S. Morphological, dielectric and electrical conductivity characteristics of clay-containing nanohybrids of poly (N-vinylcarbazole) and polypyrrole. *J. Nanosci. Nanotech.* **Vol. 12**, P. 7841-7848 (2012). DOI: 10.1166/jnn.2012.6589.
21. Haldar, I., Biswas, M., **Nayak, A.** and Sinha Ray, S. Dielectric Properties of Polyaniline-Montmorillonite Clay Hybrids. *J. Nanosci. Nanotech.* **Vol. 13 (1-6)**, P. 1824-1829 (2013). DOI: 10.1166/jnn.2013.7125.
22. **Nayak, A.** and Bhunia, S. Microstructure and dielectric functions of Ge nanocrystals embedded between amorphous Al₂O₃ films: study of confinement and disorder. *J. Exptl. Nanosci.* **Vol. 9**, 463-474 (2014). DOI:10.1080/17458080.2012.669852.
23. Haldar, I., Biswas, M., and **Nayak, A.** Dielectric and Conductivity Characteristics of CuCl₂ Doped Poly (N-vinyl carbazole) and Its Hybrid Nanocomposites with Fe₃O₄. *J. Nanosci. Nanotech.* **Vol. 14 (N.8)**, P. 5774-5778 (2014). DOI: 10.1166/jnn.2014.8885.
24. Haldar, I., Biswas, M., and **Nayak, A.** Some Observations on the Dielectric and Conductivity Behavior of Nanocomposites of Polyaniline with Fe₃O₄ and CuFe₂O₄. *Polymer-Plastics Technol. & Engg.* **Vol. 53**, P. 1317-1326 (2014). DOI: 10.1080/03602559.2014.886118.

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2. Pradhan, A., Maitra, T., Mukherjee, S., Mukherjee S., **Nayak, A.**, Satpati, B., Bhunia, S. (2016) Observation of Natural Superlattice in Al_xGa_{1-x}As Layers Grown by Metalorganic Vapour Phase Epitaxy. *AIP Conf. Proc.* **Vol. 1728**, P. 020243-1-020243-6; DOI:10.1063/1.4946294.
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- [Nanomaterials \(ICLAN\)](#); held at Saha Institute of Nuclear Physics Campus, Kolkata. November 10 – December, 2006.
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 9. **Mukherjee, S., Maitra, T., Nayak, A.,** Pradhan, A., Mukherjee, S., Bhunia, S. Interface characteristics of ZnSnP₂/Si heterostructure studied by x-ray reflectivity measurement. [ISSMD 4 Symposium](#), Organized by School of materials science and Nanotechnology, Jadavpur University, **Venue:** Jadavpur University, West Bengal. **Date:** 8th-10th March 2017.
 10. **Maitra, T.,** Pradhan, A., **Mukherjee, S.,** Mukherjee, S., **Nayak, A.**, Bhunia, S. Metal Organic Chemical Vapor Deposition growth and characterization of (Al_yGa_{1-y})_xIn_(1-x)P/GaAs semiconductor heterostructures. [National Conference on Nanotechnology: Materials and Applications \(NCoN:M&A\)](#), Organized by School of materials science and Nanotechnology, Jadavpur University, **Venue:** Jadavpur University, West Bengal. **Date:** 16th-17th June 2016.
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14. **Maitra, T., Mukherjee, S., Rahman, M., Pradhan, A., Mukherjee, S., Nayak, A., Bhunia, S.** Investigation of Structural, Optical, and Multiferroic properties of Chromium Doped Nanocrystalline $GdFeO_3$, [NCFMP 2018 Organized by Adamas University](#), **Venue:** Barasat, West Bengal. August 16-17, 2018.
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16. **Maitra, T., Mukherjee, S., Pradhan, A., Mukherjee, S., Nayak, A., Bhunia, S.** Visible-NIR photodetector based on Au-Ge/ $(Al_yGa_{1-y})_x In_{1-x}P$ /Ni asymmetric coplanar metal-semiconductor-metal structure, [IWPSD 2019, XXth International Workshop on Physics of Semiconductor Devices: IWPSD 2019](#), **Venue:** Novotel Hotel and Residences, Kolkata, India. **Date:** December 17-20, 2019.

CREATION OF RESEARCH FACILITY AND INFRASTRUCTURE DEVELOPMENT

- DST FIST Program: I am always being actively involved for planning and procuring valuable equipment to the Department for creating infrastructure facilities. Many valuable instruments like UV-Vis-NIR spectrophotometer with reflectance measurement facility (Perkin Elmer, Lambda-750), Vacuum coating unit (Hind High vacuum Co Ltd.), FTIR spectrometer (Spectrum 2, Perkin Elmer), Electrochemical Workstation (CH Instruments) etc. have been successfully installed in the Department.
- I have taken a leading part for the creation of substantial instrumental facilities for research and teaching. A new generation sophisticated XRD (PANalytical X'PERT PRO) machine was commissioned and installed in the year 2010 under my direct supervision. This equipment was purchased from the development grant (2009-10) received from the Govt. of West Bengal.
- One HIOKI 3532-50 LCR HiTester has also been purchased from the UGC grant under my suggestions.

MAJOR DEPARTMENTAL COMMITTEES MEMBERS

- DST-FIST Program Monitoring Committee
- Purchase Committee
- Departmental Academic & PhD Committee

MAJOR UNIVERSITY COMMITTEES MEMBER & CHAIRPERSONS

- Purchase-Cum Tender Committee 2013-2019
- Chairman, University Admission Committee 2016-2019
- Member, Finance Committee 2016-2019
- Member, Governing Body, Presidency University 2016-2019
- Member, University Doctorate Committee (Sciences)
- Member, Faculty Council (Sciences)

MAJOR ADMINISTRATIVE RESPONSIBILITY (PAST)

- Head of the Department of Physics, Darjeeling Govt. College 2001-2002
- Assistant Superintendent (Government Eden Hindu Hostel) 2002-2004
- In many occasions I have been given the responsibilities normally assumed by the Head of the Department.

MAJOR ADMINISTRATIVE RESPONSIBILITY

1. **Professor-in-Charge**, Library Services, Presidency University 2016-till date.
In addition to the routine work, my involvement to the ongoing program related to the modernization of library services:
 - User awareness program of e-resources
 - Awareness program against plagiarism using TURNITIN software
 - Off campus e-resources under virtual private net-work (VPN)
 - Development of Institutional Repository: Digitization and making the digital copy available to all through web for the important manuscripts and magazines of Presidency College/University has been started.
 - Complete rearrangement of collections: Books are properly classified and rearranged. Initiatives have been taken to automate the library services and collection properly. Real time OPAC with the facility of vernacular language searching and actual status of the document along with the online request, email and SMS facility to the users have been started.
2. **Nodal Officer**, Undergraduate and Postgraduate Admissions, Presidency University.
3. **Director**, Internal Quality Assurance Cell (IQAC), Presidency University 2019-till date.

(Aravinda Nayak)